

FAST RECOVERY DIODE

Features

- Surface mount device
- High voltage by mesa design
- High reliability

Applications

- High speed switching

Maximum ratings and characteristics

- Absolute maximum ratings

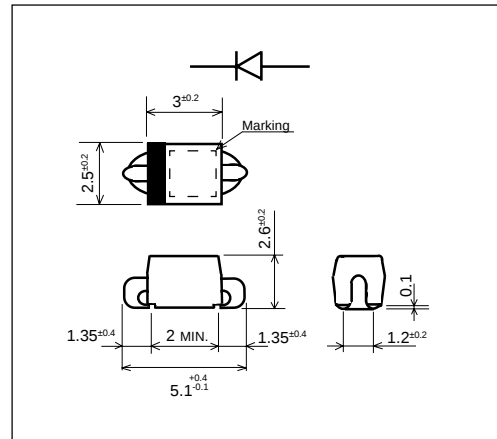
Item	Symbol	Conditions	Rating	Unit
			-02	
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		200	V
Average output current	I_o	Resistive load ($T_a=25^{\circ}\text{C}$)	1.0*	A
Surge current	I_{FSM}	Sine wave 10ms	40	A
Operating junction temperature	T_j		-40 to +150	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-40 to +150	$^{\circ}\text{C}$

*Mounted to glass fabric base epoxy resin printed circuits, land (15mm x 15mm)

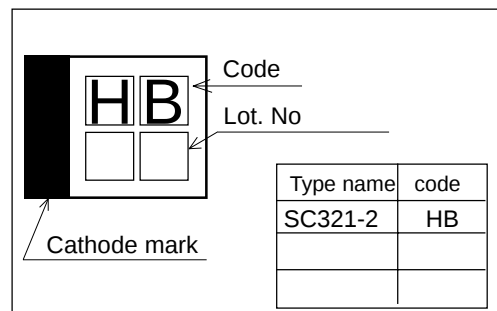
- Electrical characteristics ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=1.0\text{A}$	1.05	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	50	μA
Reverse recovery time	t_{rr}	$I_F=0.1\text{A}$, $I_R=0.1\text{A}$	100	ns
Thermal resistance	$R_{th(j-a)}$	Junction to ambient	120*	$^{\circ}\text{C/W}$

Outline drawings, mm

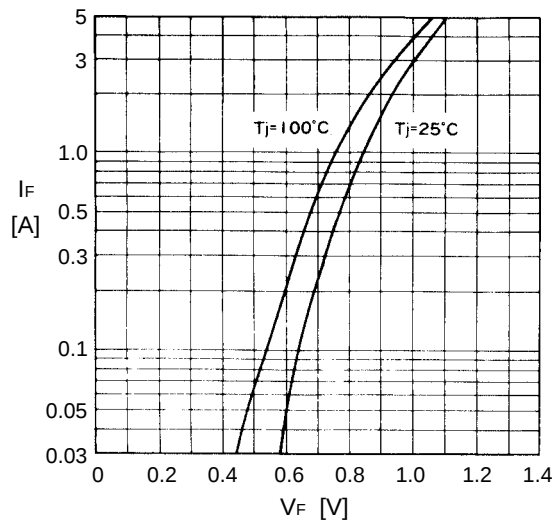


Marking

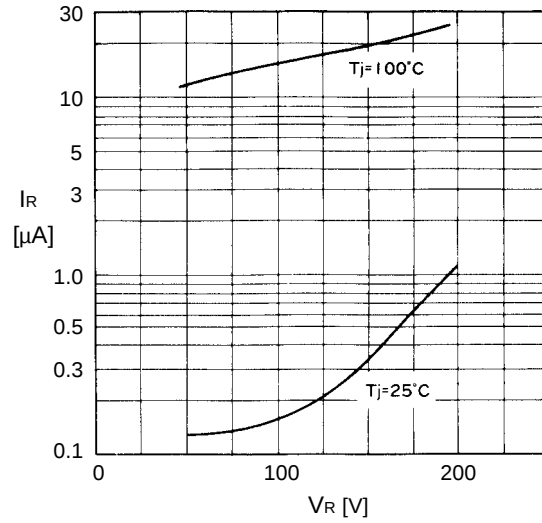
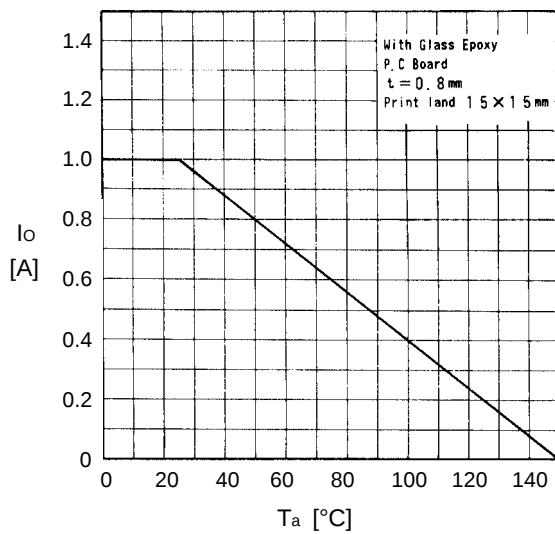


Characteristics

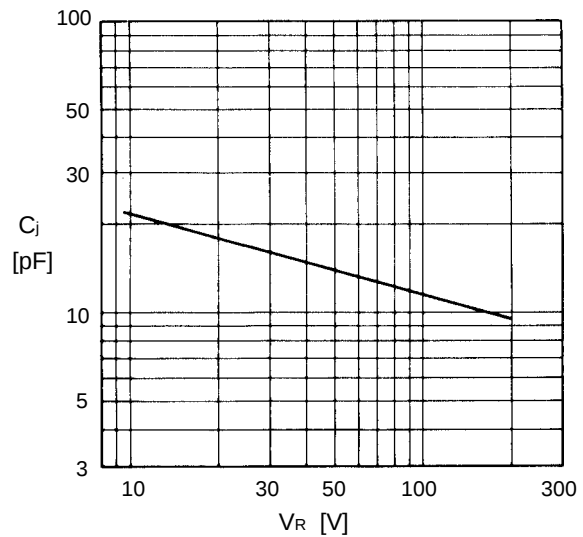
Forward characteristics



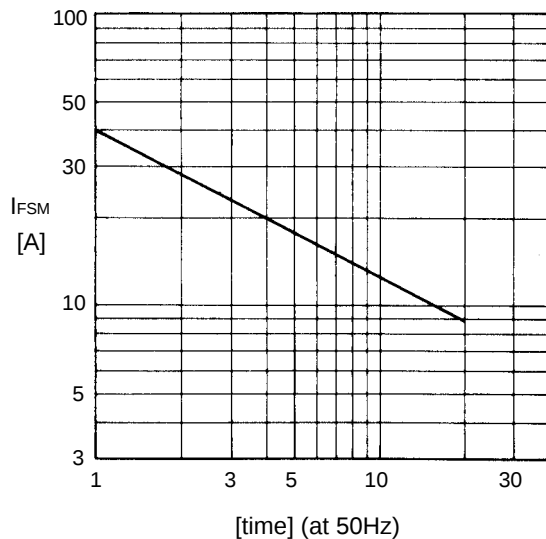
Reverse characteristics

Current derating ($I_o - T_a$)

Junction capacitance characteristics



Surge capability



Thermal resistance print land

